

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Extended temperature range T_i = 175 °C
- Side wettable flanks for optical solder inspection
- ElectroStatic Discharge (ESD) protection > 1 kV HBM (class H1C)
- Trench MOSFET technology
- AEC-Q101 qualified

3. Applications

- DC to DC conversion
- High-speed line driver
- High-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	T _j = 25 °C	-	-	-20	V
V _{GS}	gate-source voltage		-12	-	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{sp} = 25 °C	-	-	-18	А
P _{tot}	total power dissipation	T _{sp} = 25 °C	-	-	19	W
Static chara	octeristics					
R _{DSon}	drain-source on-state resistance	V _{GS} = -4.5 V; I _D = -6 A; T _j = 25 °C	-	30	38	mΩ



5. Pinning information

Table 2	Table 2. Pinning information								
Pin	Symbol	Description	Simplified outline	Graphic symbol					
1	D	drain		D					
2	D	drain							
3	G	gate	2						
4	S	source	3 8 4						
5	D	drain	Transparent top view						
6	D	drain	DFN2020MD-6 (SOT1220)	s					
7	D	drain		017aaa259					
8	S	source							

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BUK4D38-20P		plastic, leadless thermal enhanced ultra thin small outline package with side-wettable flanks (SWF); 6 terminals; 0.65 mm pitch; 2 mm x 2 mm x 0.65 mm body	SOT1220			

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK4D38-20P	6F

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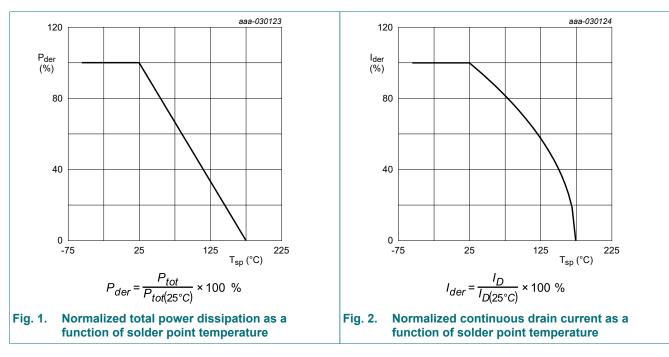
8. Limiting values

Table 5. Limiting values

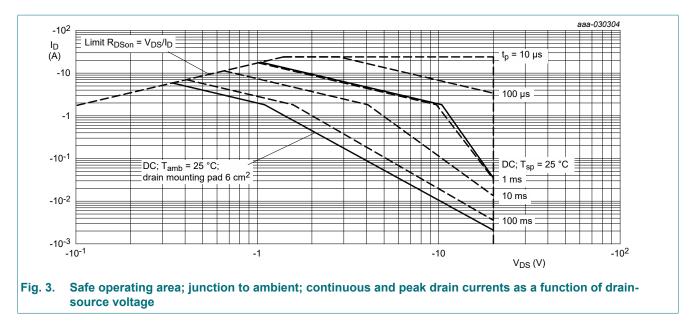
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V _{GS}	gate-source voltage	_		-12	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{sp} = 25 °C		-	-18	А
		V _{GS} = -4.5 V; T _{sp} = 100 °C		-	-11	А
		V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-6	А
I _{DM}	peak drain current	T_{sp} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	-72	А
P _{tot}	total power dissipation	T _{sp} = 25 °C		-	19	W
		T _{amb} = 25 °C	[1]	-	2	W
Tj	junction temperature			-55	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C
Source-drain	n diode					
I _S	source current	T _{sp} = 25 °C		-	-19	А
		T _{amb} = 25 °C	[1]	-	-2	А
I _{SM}	peak source current	single pulse; $t_p \le 10 \ \mu s$; $T_{sp} = 25 \ ^{\circ}C$		-	-75	А
ESD maximu	um rating		·			
V _{ESD}	electrostatic discharge voltage	НВМ	[2]	-	1000	V
Avalanche r	uggedness		·			
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	T _{j(init)} = 25 °C; I _D = 1.5 A; DUT in v avalanche (unclamped)		-	15	mJ
	I					

Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².
 Measured between all pins.



20 V, P-channel Trench MOSFET

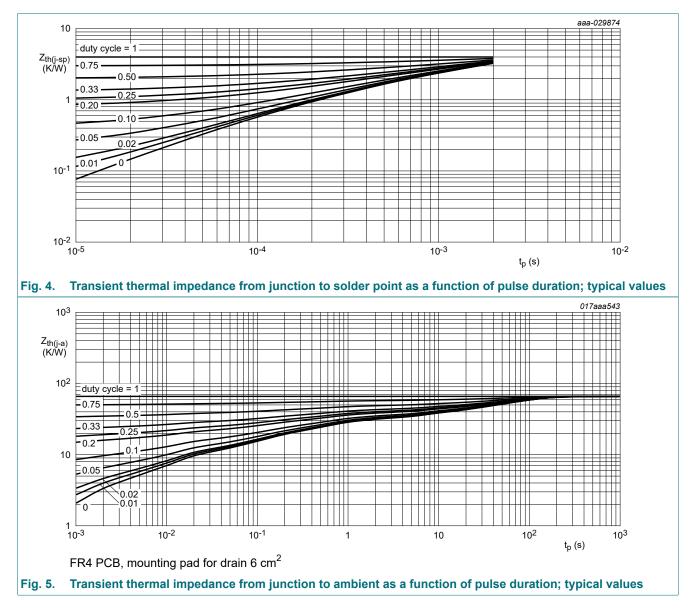


BUK4D38-20P

9. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	66	76	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	4	8	K/W

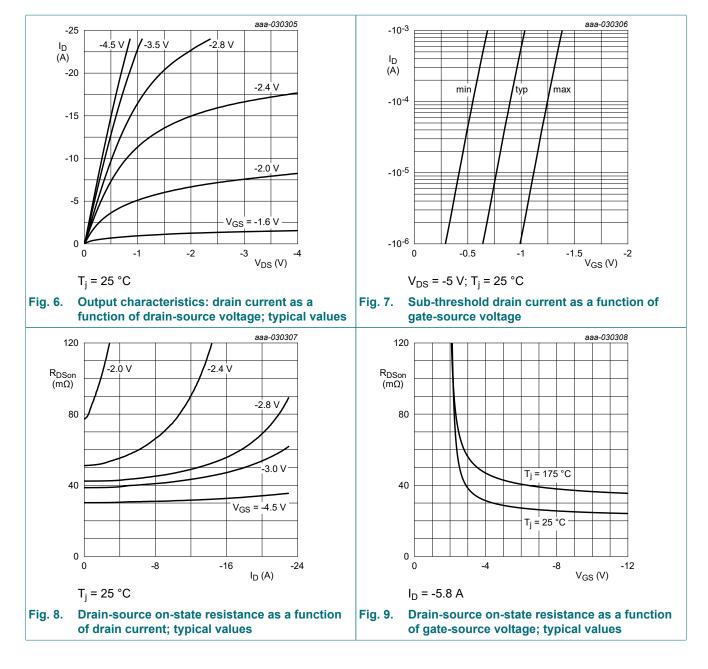
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².



10. Characteristics

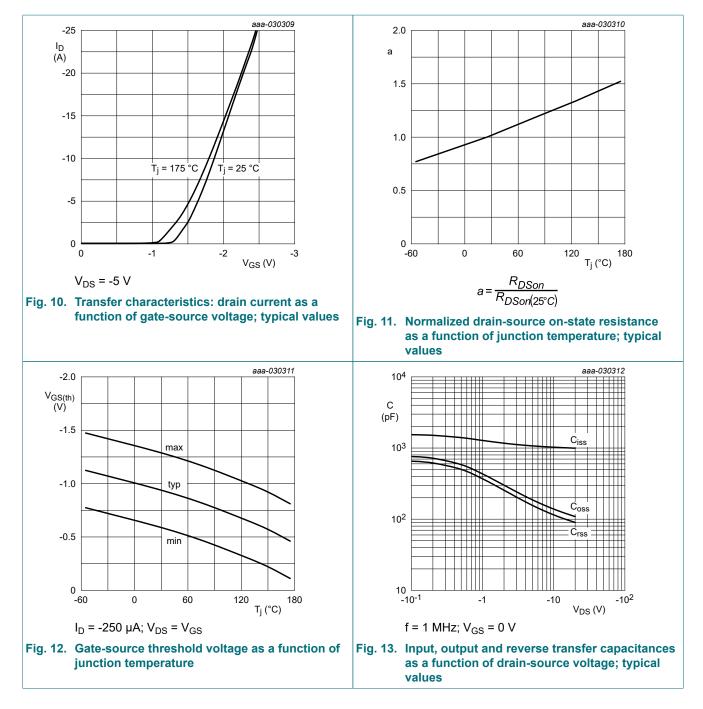
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I _D = -250 μA; V _{GS} = 0 V; T _j = 25 °C	-20	-	-	V
V _{GSth}	gate-source threshold voltage	I_D = -250 µA; V_{DS} = V_{GS} ; T_j = 25 °C	-0.6	-0.95	-1.3	V
I _{DSS}	drain leakage current	V_{DS} = -20 V; V_{GS} = 0 V; T_j = 25 °C	-	-	-1	μA
		V _{DS} = -20 V; V _{GS} = 0 V; T _j = 125 °C	-	-	-20	μA
I _{GSS}	gate leakage current	V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
		V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
		V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-2	μA
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	2	μA
R _{DSon}	drain-source on-state resistance	V _{GS} = -8 V; I _D = -6 A; T _j = 25 °C	-	26	33	mΩ
		V _{GS} = -8 V; I _D = -6 A; T _j = 175 °C	-	40	50	mΩ
		V _{GS} = -4.5 V; I _D = -6 A; T _j = 25 °C	-	30	38	mΩ
		V _{GS} = -2.5 V; I _D = -2 A; T _j = 25 °C	-	46	64	mΩ
9fs	forward transconductance	V _{DS} = -10 V; I _D = -6 A; T _j = 25 °C	-	20	-	S
R _G	gate resistance	f = 1 MHz	-	21	-	Ω
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = -10 V; I_{D} = -5.8 A; V_{GS} = -4.5 V;	-	10.6	16	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	2.1	-	nC
Q _{GD}	gate-drain charge		-	3.6	-	nC
C _{iss}	input capacitance	V _{DS} = -10 V; f = 1 MHz; V _{GS} = 0 V;	-	1025	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	137	-	pF
C _{rss}	reverse transfer capacitance		-	113	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I _D = -5.8 A; V _{GS} = -4.5 V;	-	6	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	17	-	ns
d(off)	turn-off delay time	-	-	23	-	ns
f	fall time	1	-	19	-	ns
Source-drai	in diode		1			
V _{SD}	source-drain voltage	I _S = -2 A; V _{GS} = 0 V; T _j = 25 °C	-	-0.8	-1.2	V
rr	reverse recovery time	$I_{S} = -2 \text{ A}; \text{ d}I_{S}/\text{d}t = 100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$	-	17	-	ns
Q _r	recovered charge	V _{DS} = -10 V; T _j = 25 °C	_	5	_	nC

20 V, P-channel Trench MOSFET

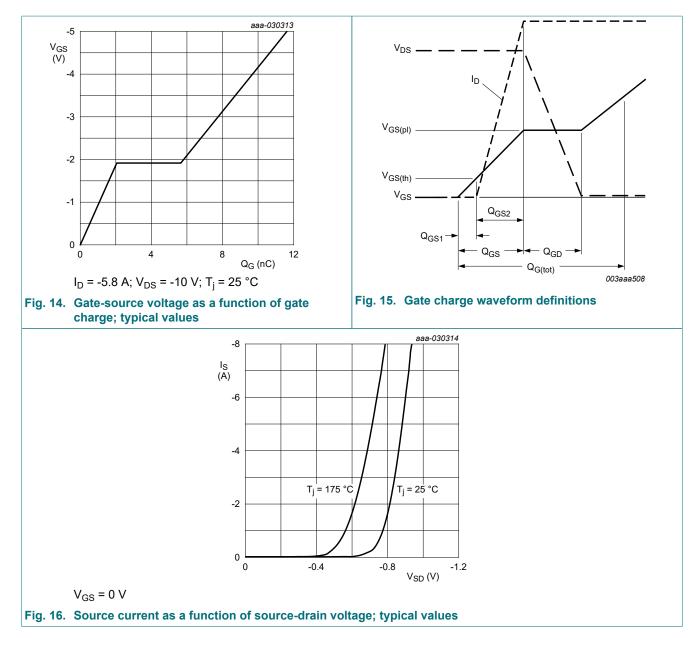


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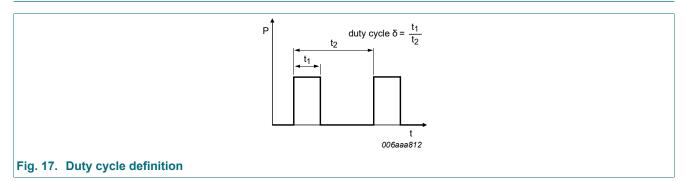
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20 V, P-channel Trench MOSFET



11. Test information

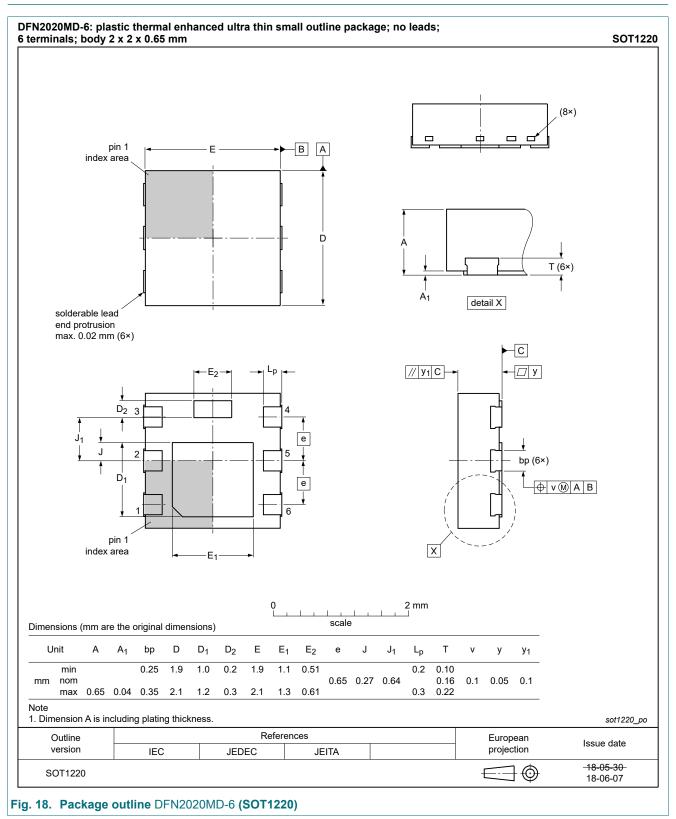


Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

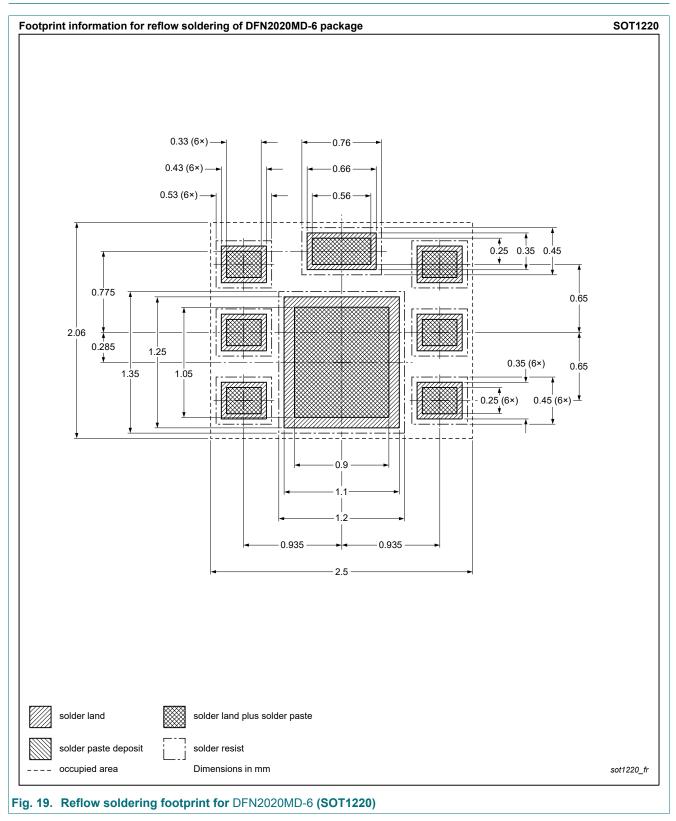
20 V, P-channel Trench MOSFET

12. Package outline



20 V, P-channel Trench MOSFET

13. Soldering



14. Revision history

Table 8. Revision history Data sheet ID Release date Data sheet status Change notice Supersedes							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
BUK4D38-20P v.3	20200709	Product data sheet	-	BUK4D38-20P v.2			
Modifications:	Product status	changed.	•				
BUK4D38-20P v.2	20200121	Objective data sheet	-	BUK4D38-20P v.1			
BUK4D38-20P v.1	20191025	Objective data sheet	-	-			

BUK4D38-20P

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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20 V, P-channel Trench MOSFET

Contents

1. Gene	ral description	1
2. Featu	res and benefits	1
3. Appli	cations	1
4. Quick	reference data	1
5. Pinnii	ng information	2
6. Order	ring information	2
7. Marki	ing	2
8. Limiti	ing values	3
9. Thern	nal characteristics	5
10. Chai	racteristics	6
11. Test	information	10
12. Pack	kage outline	11
	lering	
14. Revi	ision history	13
	al information	
-		

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